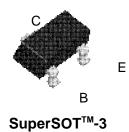


FMMT449



NPN Low Saturation Transistor

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous. Sourced from Process NB.

Absolute Maximum	Ratings*	T _{A = 25°C} unless otherwise noted
-------------------------	----------	----------------------------------------------

Symbol	Parameter	FMMT449	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous - Peak Pulse Current	1 2	А
T _{J,} T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_{A = 25°C unless otherwise noted}

Symbol	Characteristic	Мах	Units
		FMMT449	
P _D	Total Device Dissipation* Derate above 25°C	500 4	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

^{*}Device mounted on FR-4 PCB 4.5" X 5"; mounting pad 0.02 in 2 of 2oz copper.

INFINITOR SATURATION TRANSIS	NPN I	turation Transisto
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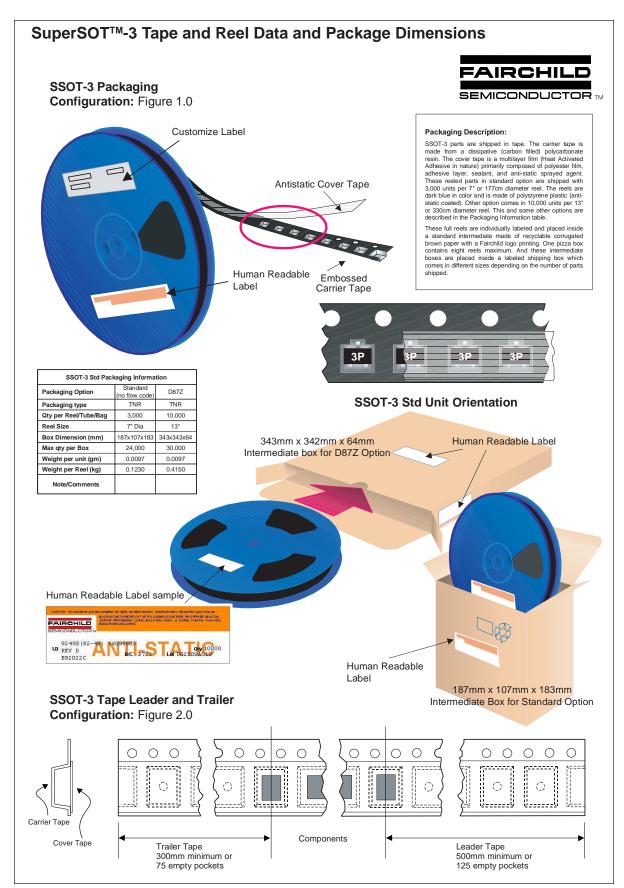
(continued)

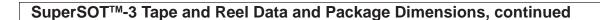
Electrical Characteristics

 $T_{A=25^{\circ}\text{C}}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS			•	
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	30		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1mA	50		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA	5		V
Сво	Collector Cutoff Current	V _{CB} = 40 V V _{CB} = 40 V, Ta=100°C		100 10	nA uA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA
ON CHAR	ACTERISTICS*				
h _{FE}	DC Current Gain	$I_C = 50$ mA, $V_{CE} = 2V$	70		-
		$I_C = 500 \text{ mA}, V_{CE} = 2V$	100	300	
		$I_C = 1A$, $V_{CE} = 2V$	80		
		$I_C = 2A$, $V_{CE} = 2V$	40		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		500	mV
02(00.)		I _C = 2 A, I _B = 200 mA		1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		1.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 2 V		1	V
SMALL SI	GNAL CHARACTERISTICS				
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		15	pF
f _T	Transition Frequency	I _C = 50mA,V _{CE} = 10 V, f=100MHz	150		MHz

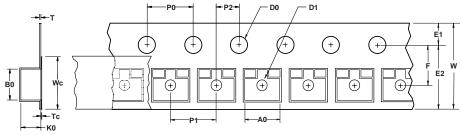
*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

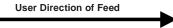




SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



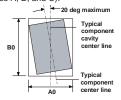


					Di	mension	s are in r	nillimeteı	•					
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

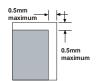
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



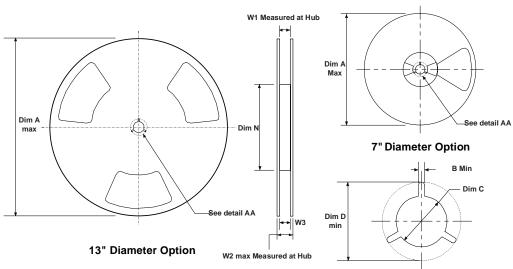
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

DETAIL AA

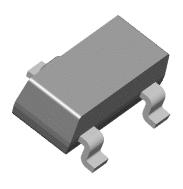
SSOT-3 Reel Configuration: Figure 4.0

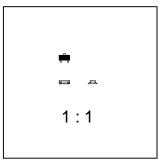


	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	

SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

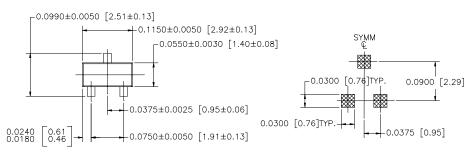
SuperSOT™-3 (FS PKG Code 32)



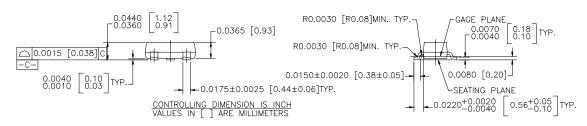


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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